



Ain Shams University
Faculty of Science
Physics Department

Electrical, Optical and Structural Studies of Some Transparent Conducting Films Prepared by Pulsed Laser Deposition

A Thesis

Submitted For The Degree of M.sc. in Science As a Partial Fulfillments
For the Requirements of the Master Degree in Science
to
physics Department, Faculty of Science,
Ain Shams University

BY

Ahmed Mohamed Abd El-Karim Ahmed

2013



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2013

Electrical, Optical and Structural Studies of Some Transparent Conducting Films
Prepared by Pulsed Laser Deposition

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The final copy of this thesis has been examined by the signatories, and we find that both the content and form meet acceptable presentation standards of scholarly work in the above mentioned discipline.

I hereby declare that the work contained in this thesis, now submitted for the degree of master of Science (Physics) to Ain Shams University, is the result of my own investigation.

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I hereby certify that the work embodied in this thesis has not already accepted in substance for any degree, and is not currently being submitted for any other degree.

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CONTENTS

Page

ABSTRACT

CHAPTER (I): INTRODUCTION AND LITERATURE

REVIEW

1.1. Transparent Conducting Oxide	1
1.2. Indium Tin Oxide (ITO)	2
1.3. Physical Structure and Properties of ITO	3
1.4. Thin film Deposition Techniques	4
1.4.1. Chemical Vapor Deposition (CVD)	5
1.4.2. Sputtering	6
1.4.3. Thermal Evaporation	6
1.4.4. Spray Pyrolysis	7
1.4.5. Screen Printing Technique	7
1.4.6. Pulsed Laser Deposition (PLD)	8
1.5. Why Grow Compound Semiconductors by PLD?	11
1.6. Application of TCO	12
1.7. Literature Review	13
1.8. Aims and Objectives	23

CHAPTER (II): THEORETICAL CONCEPTS

2.1. Ultrafast Femtosecond Laser	24
2.1.1. Chirped Pulse Amplification (CPA)	24
2.1.1.1. The Seed Laser (Femtosecond Oscillators)	26
2.1.1.2. Stretcher Stage	27
2.1.1.3. Laser Amplification Stage	28
2.1.1.4. Compressor Stage	29
2.2. Pulsed Laser Deposition Technique (PLD)	29
2.2.1. Mechanism of PLD	30
2.3. X-Ray Diffraction (XRD)	33
2.3.1. Fundamental Principles of X-ray Diffraction	33
2.3.2. The Bragg Equation	33
2.3.3. Determination of Unit Cell Dimension a_0	34

2.3.4. Crystallite Size Determination from Line	34
2.4. Origin of Absorption Spectra	34
2.4.1. Ultraviolet and Visible Spectroscopy	36
2.4.1.1. Optical Absorption Coefficient	37
2.4.1.2. Burstein–Moss effect	39
2.5. Semiconductors from Bulk Materials to Quantum Confinement	40
2.5.1. Energy Band Theory	40
2.5.2. Bulk Semiconductor	42
2.5.3. Quantum Confinement Effect	43
2.6. Electron Microscopy	46
2.6.1. Transmission Electron Microscope (TEM)	46
2.6.1.1. Imaging and Diffraction in Transmission Electron Microscope	47
2.6.2 Scanning Electron Microscope (SEM)	49
2.7. Four-Point Probe (4-point probe)	51

CHAPTER (III): EXPERIMENTAL TECHNIQUES AND INSTRUMENTATION

3.1. Samples Preparation	53
3.1.1. Substrates Preparation	53
3.1.2. Preparation of ITO thin films	53
3.2. Characterization Techniques	55
3.2.1. X-ray Diffraction (XRD)	55
3.2.2. Ultraviolet Visible Spectrophotometer (UV-Vis)	56
3.2.3. Four-Point Probe Manual (4-point probe)	57
3.2.4. Transmission Electron Microscope (TEM)	58
3.2.5. Scanning Electron Microscope (SEM)	59
3.2.6. Stylus Profile	60

CHAPTER (IV): RESULTS AND DISCUSSION

4.1. Effect of Deposition Temperature	62
4.1.1. X-ray Diffraction Analysis	63
4.1.2. Optical properties	68
4.1.3. Electrical properties	78
4.2. Effect of Vacuum Annealing	80

4.2.1. X-ray Diffraction Analysis	80
4.2.2. Optical properties	83
4.2.3. Electrical properties	86
4.3. Effect of Oxygen Environment during Deposition	88
4.3.1. X-ray Diffraction Analysis	89
4.3.2. Optical properties	91
4.3.3. Electrical properties	94
4.4. Deposition under medium vacuum 10^{-4} torr	97
4.4.1. X-ray Diffraction Analysis	97
4.4.2. Optical properties	99
4.4.3. Electrical properties	102
4.5. Transmission Electron Microscope (TEM)	103
4.6. Scanning Electron Microscope (SEM)	108

Conclusion**Reference****Arabic Summary**

LIST OF TABLES

No	Title	Page
4.1	Grain Size and Lattice Parameter of ITO thin films prepared under different deposition temperatures (24 - 400 °C)	67
4.2	Thickness, Average, and Max transmission of ITO thin films prepared at different deposition temperatures under vacuum base pressure 10^{-6} torr	71
4.3	Grain size of different deposition temperatures under vacuum base pressure 10^{-6} torr before and after the annealing process	83
4.4	Sheet resistance of the prepared films at different deposition temperatures before and after the vacuum annealing process	88
4.5	Grain size of ITO film prepared under two different oxygen pressures at deposition temperature 400 °C	90
4.6	Sheet resistance of the prepared thin films under different oxygen pressure and vacuum base pressure 10^{-6} torr at deposition temperature 400 °C.	96
4.7	Grain size of ITO thin film prepared under vacuum base pressure 10^{-4} torr at deposition temperature 400 °C	98
4.8	Sheet resistance of the prepared thin films under vacuum base pressure 10^{-4} torr at deposition temperature 400 °C	103

LIST OF FIGURES

No	Title	Page
1.1	Assumed parabolic band structure of undoped In_2O_3 and the effect of tin doping	4
2.1	Schematic diagram showing the chirped pulse amplification technique	25
2.2	Schematic layout of a grating-based stretcher, in this case, $L < f$, which leads to a positive dispersion	28
2.3	Schematic layout of a grating-based compressor with negative dispersion	29
2.4	Schematic represents the laser target interaction processes	33
2.5	Schematic diagram illustrating direct and indirect transition from the valence to conduction band	38
2.6	Schematic diagram showing the moss-shift effect	40
2.7	Schematic diagram showing band gaps and luminescence properties of materials (a) Band diagram for conductors, semiconductors and insulators (b) Semiconductor photoluminescence: excitation of electron from VB to CB, formation of carrier charges, emission of photon	41
2.8	The effective mass approximation of the valence band and the conduction band	43
2.9	Density of states of materials (a) Macroscopic crystal (b) Quantum dots (QDs).	45
2.10	Density of states functions plotted against energy for bulk (3-D), quantum well (2-D), quantum wire (1-D) and quantum Dot (0-D)	46
2.11	Schematic diagram showing the Transmission Electron Microscope (TEM)	49
2.12	Schematic diagram showing the Scanning Electron Microscope (SEM)	51
2.13	Schematic of 4-point probe configuration	52
3.1	Schematic diagram of the Pulsed Laser Deposition Technique	54
3.2	Ultrafast Femtosecond Laser System	54
3.3	Ultrahigh Vacuum system	55
3.4	Panalytical – Empyrean, X-ray Diffractometer	56
3.5	V-570 UV/VIS/NIR Jasco Spectrophotometer	57

List of Figures

No	Title	Page
3.6	4-point probe, Model 1906 Computing Multimeter, Thurlby Thander	58
3.7	Transmission Electron Microscope (TEM) Jeol - JEM-1011	59
3.8	Scanning Electron Microscope (SEM) Inspects FEI Philipes Company, Netherlands	60
3.9	Schematic diagram illustrating the determination of thin film thickness with Stylus Profiler	61
4.1	X-ray spectra of ITO thin films prepared at different deposition temperatures under vacuum base pressure 10^{-6} torr.	65
4.2	UV-Vis-NIR transmission spectra of ITO thin films prepared at different deposition temperatures under vacuum base pressure 10^{-6} torr	69
4.3	UV-Vis-NIR reflection spectra of ITO thin films prepared at different deposition temperatures under vacuum base pressure 10^{-6} torr	70
4.4	Relation between absorption coefficient and wavelength for ITO thin films prepared at different deposition temperature under vacuum base pressure 10^{-6} torr	72
4.5	Schematic shows the grain boundary scattering for two different grain sizes	73
4.6	Variation of $(\alpha h\nu)^2$ with $h\nu$ for ITO thin films prepared at deposition temperature 200 °C under vacuum base pressure 10^{-6} torr	75
4.7	Variation of $(\alpha h\nu)^2$ with $h\nu$ for ITO thin films prepared at deposition temperature 300 °C under vacuum base pressure 10^{-6} torr	76
4.8	Variation of $(\alpha h\nu)^2$ with $h\nu$ for ITO thin films prepared at deposition temperature 400 °C under vacuum base pressure 10^{-6} torr	76
4.9	Schematic illustrates the conduction band filling due to heavily doped n-type doping	77
4.10	Sheet resistance of ITO thin films prepared under vacuum base pressure 10^{-6} torr at different deposition temperatures	79
4.11	X-ray spectra of ITO thin films prepared under vacuum base pressure 10^{-6} torr at deposition temperature 24 °C	81

No	Title	Page
4.12	X-ray spectra of ITO thin films after the annealing process for samples prepared under vacuum base pressure 10^{-6} torr under deposition temperatures (24, 100 and 400 °C)	82
4.13	UV-VIS-NIR transmission spectra of ITO thin films prepared under vacuum base pressure 10^{-6} torr at different deposition temperatures after the annealing process	84
4.14	Average transmission spectra of ITO thin films at the optical range (400-800) nm for the as-deposited and annealed thin films	85
4.15	Sheet resistance of ITO thin films prepared under vacuum base pressure 10^{-6} torr at different deposition temperatures before and after the annealing process	87
4.16	X-ray spectra of ITO thin films prepared at deposition temperature 400 °C and oxygen pressure 1 mtorr	90
4.17	X-ray spectra of ITO thin films prepared at deposition temperature 400 °C and oxygen pressure 10 mtorr	90
4.18	UV-VIS-NIR transmission spectra of ITO thin films prepared under different oxygen pressure at deposition temperature 400 °C	92
4.19	UV-VIS-NIR reflection spectra of ITO thin films prepared under different oxygen pressure at deposition temperature 400 °C	93
4.20	Variation of $(\alpha h\nu)^2$ with $h\nu$ for ITO thin films prepared under oxygen pressure 1 mtorr at deposition temperature 400 °C	94
4.21	Variation of $(\alpha h\nu)^2$ with $h\nu$ for ITO thin films prepared under oxygen pressure 10 mtorr at deposition temperature 400 °C	94
4.22	X-ray spectra of ITO thin films prepared under vacuum base pressure 10^{-4} torr at deposition temperature 400 °C	98
4.23	UV-VIS-NIR transmission spectrum of ITO thin film prepared under vacuum base pressure 10^{-4} torr at deposition temperature 400 °C	100
4.24	UV-VIS-NIR reflection spectrum of ITO thin film prepared under vacuum base pressure 10^{-4} torr at deposition temperature 400 °C	101
4.25	Variation of $(\alpha h\nu)^2$ with $h\nu$ for ITO thin films prepared under vacuum base pressure 10^{-4} torr at deposition	102

List of Figures

No	Title	Page
	temperature 400 °C	
4.26	TEM image of ITO nanoparticle prepared at deposition temperature 200 °C under vacuum base pressure 10^{-6} torr	105
4.27	TEM image of ITO nanoparticle prepared at deposition temperature 300 °C under vacuum base pressure 10^{-6} torr	106
4.28	TEM image of ITO nanoparticle prepared at deposition temperature 400 °C under vacuum base pressure 10^{-6} torr	106
4.29	TEM image of ITO nanoparticle prepared at deposition temperature 400 °C and oxygen pressure 1 mtorr	107
4.30	TEM image of ITO nanoparticle prepared at deposition temperature 400 °C and oxygen pressure 10 mtorr	107
4.31	TEM image of ITO nanoparticle prepared at deposition temperature 400 °C under vacuum base pressure 10^{-4} torr	108
4.32	SEM image of ITO thin film prepared at deposition temperature 24 °C and vacuum base pressure 10^{-6} torr	109
4.33	SEM image of ITO thin film prepared at deposition temperature 400 °C and vacuum base pressure 10^{-6} torr	109
4.34	SEM image of ITO thin film prepared at deposition temperature 24 °C after the annealing process	110
4.35	SEM image of ITO thin film prepared at deposition temperature 400 °C with oxygen pressure 1 mtorr	111
4.36	SEM image of ITO thin film prepared at deposition temperature 400 °C under vacuum base pressure 10^{-4} torr	111
